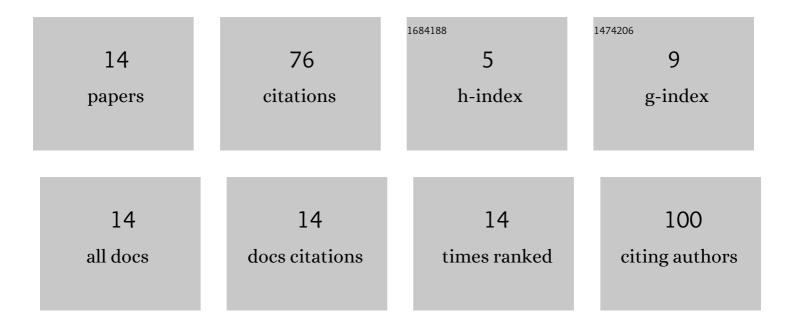
## Mahitosh Biswas

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Thermodynamically metastable <b>α</b> -, <b>ε</b> - (or <b>β</b> -), and <b>γ</b> -Ga2O3: From material growth to device applications. APL Materials, 2022, 10, .	5.1	23
2	Growth of high quality (In,Ga)N films on O-face ZnO substrates by plasma-assisted molecular beam epitaxy. AIP Advances, 2020, 10, .	1.3	4
3	Effects of rapid thermal annealing in InGaN/GaN quantum disk-in-GaN nanowire arrays. Journal of Luminescence, 2020, 222, 117123.	3.1	2
4	Engineering of carrier localization in BGaAs SQW for novel intermediate band solar cells: Thermal annealing effect. Solar Energy, 2020, 199, 183-191.	6.1	12
5	Enhanced optical and structural properties of MBE-grown AlGaN nanowires on Si substrate by H-ion implantation and UV ozone treatment. , 2019, , .		1
6	Passivation of Surface States of AlGaN Nanowires Using H <sub>3</sub> PO <sub>4</sub> Treatment To Enhance the Performance of UV-LEDs and Photoanodes. ACS Applied Nano Materials, 2018, 1, 1968-1975.	5.0	9
7	Vertical strain-induced dot size uniformity and thermal stability of InAs/GaAsN/GaAs coupled quantum dots. Journal of Alloys and Compounds, 2018, 748, 601-607.	5.5	4
8	Ultrathin GaAsN matrix-induced reduced full width at half maximum of GaAsN/InAs/GaAsN dot-in-a-well heterostructures with extended emission wavelength. Journal of Luminescence, 2018, 194, 341-345.	3.1	5
9	High nitrogen composition–induced low interfacial roughness of GaAs 0.978 N 0.022 /GaAs multiple quantum wells grown through solid-source molecular beam epitaxy. Materials Research Bulletin, 2017, 88, 242-247.	5.2	3
10	Varying nitrogen background pressure; an efficient approach to improve electrical properties of MBE-grown GaAs1â^'xNx thin films with less atomic disorder. Journal of Alloys and Compounds, 2017, 695, 3163-3169.	5.5	7
11	Annihilation of arsenic-nitrogen bonding defects in annealed InAs1â^'xNx quantum dots grown through nitrogen background pressure–controlled SS-MBE. Journal of Alloys and Compounds, 2017, 722, 287-292.	5.5	1
12	A low temperature investigation of the optical properties of coupled InAs quantum dots with GaAsN/GaAs spacers. Proceedings of SPIE, 2017, , .	0.8	1
13	Defect annihilation-mediated enhanced activation energy of GaAs 0.979 N 0.021 -capped InAs/GaAs quantum dots by H â~' ion implantation. Thin Solid Films, 2017, 639, 73-77.	1.8	4
14	CAD Model to Predict the Effect of Radome on the Characteristics of Rectangular Patch Antenna. Microwave and Optical Technology Letters, 2013, 55, 2460-2468.	1.4	0